



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

2SC4548 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 500 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 200 mA

Collector-base voltage

$V_{(BR)CBO}$: 400 V

Operating and storage junction temperature range

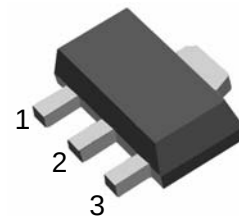
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=300V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10V, I_C=50mA$	60		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50mA, I_B=5mA$			1	V
Transition frequency	f_T	$V_{CE}=30V, I_C=10mA$		70		MHz
Collector output capacitance	C_{ob}	$V_{CB}=30V, I_E=0, f=1MHz$		4		pF
Turn-ON Time	t_{on}	$V_{CC}=150V, I_C=50mA,$ $I_{B1}=-I_{B2}=5mA$		0.25		μs
Turn-OFF Time	t_{off}			5		μs

CLASSIFICATION OF $h_{FE(1)}$

Rank	D	E
Range	60-120	100-200
Marking	CN	